

N85-32435

SILICON DENDRITIC WEB GROWTH

WESTINGHOUSE ELECTRIC CORP.

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<u>Technology</u> Single crystal ribbon growth	<u>Report Date</u> 10/3/84
<u>Approach</u> Silicon dendritic web growth <u>Contractor</u> Westinghouse Electric Corp. Advanced Energy Systems Division JPL Contract 955843	<u>Status</u> <ul style="list-style-type: none">• 6 ½ meters of uninterrupted, continuously melt replenished web growth has been achieved with three different growth configurations• Steady-state web growth of 8 cm²/min has been achieved• Major improvement in web growth reproducibility has been achieved• Concepts for higher growth rate have been developed
<u>Goals</u> For 1984 <ul style="list-style-type: none">• Demonstrate 10 meter length of continuously melt replenish web crystal growth• Demonstrate 10 square centimeters per minute steady-state web growth	

Principal Activities This Period

- Grow Long Web Crystals From Continuously Replenished Melt
- Develop Temperature Distribution In Web And Melt
- Improve Reproducibility Of Growth
- Develop Configurations For Increased Growth Rates (Width And Speed)
- Develop New Growth System Components As Required For Improved Growth
- Evaluate Quality Of Web Grown

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Continuously Melt-Replenished Web Growth

Three Web Growth Configurations Have Achieved Long Growth (Approx. 6 Meters)

J435 (3.3 cm width)

J460L (4.1 cm width)

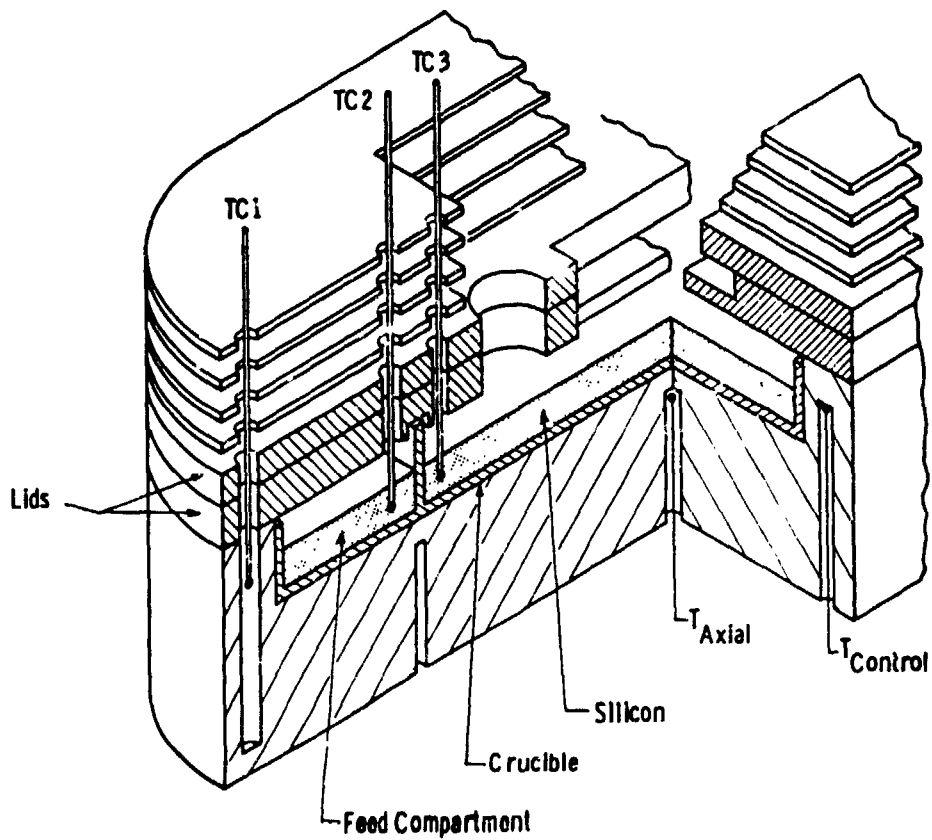
J460LS (5.1 cm width)

Critical Regions of Temperature Distribution in Silicon Web Growth

- **Between Crucible Compartments
(Growth And Melt Replenishment Compartments)**
- **Within The Growth Compartment**
- **Vertical Profile Within The Growing Web**
- **Horizontal Profile Within The Growing Web**

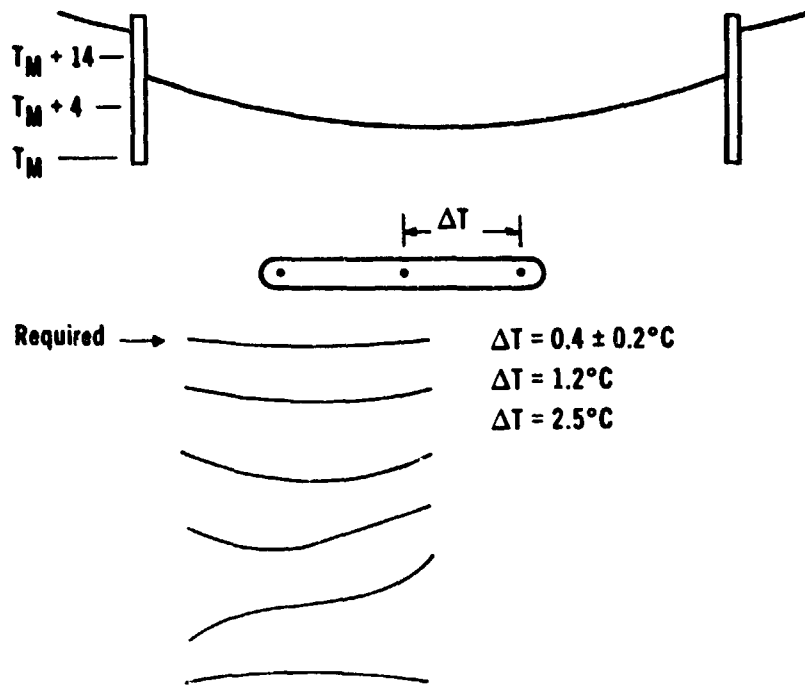
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Melt Temperature Distribution

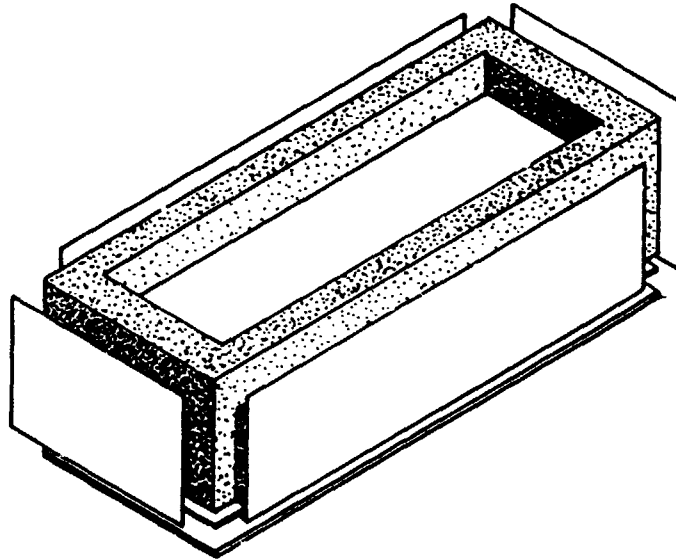


Principal Methods for Control of Melt Temperature Distribution

- Stationary Shield Configuration
- Dynamically Positionable Shield Configuration
- Dynamically Positionable Work Coil
- Design Of The Barrier Which Separates Crucible Compartments

Susceptor Shields

**For Control Of Melt Temperature Distribution Includes
Both Fixed And Adjustable Shields**



Temperature Distribution Within the Growing Web

- **Determined By Design Of The Susceptor Lids
And Top Shields**
- **Predicted By Computer Model**
- **Lid And Shield Temperatures Measured In
Growth System**

Reproducibility of Web Growth

Improvements This Period

- **Crucible Re-Designed For Better Susceptor Fit And Improved Thermal Transfer**
- **Rectangular Work Coil Fabricated With Precision Dimensions**
- **Perimeter Shields Re-Designed For Reproducible Spacing**
- **Mated Parts Fitted For Uniform Thermal Transfer**

**Configurations for Increased Growth Rates
(Width and Speed)**

- **Concepts Are Generated Through Computer Modeling**
- **Initial Design Specification Derived From Models**
- **Design Is Verified Through Experimental Web Growth**
- **Experimental Web Growth And Measurements Provide Data For Additional Input To Model**

Growth System Component Development

Major Examples Of Component Development In This Reporting Period:

New Crucibles

Improved Crucible Barriers

New Induction Heating Work Coils

New Furnace Cover Plate For Higher Growth Rate

Improved Feeder For Polysilicon Pellets

Thermal Elements For New Growth System Designs

**Instrumentation For Monitoring Dendrite Thickness
(Incomplete)**

Web Quality Evaluation

Sources

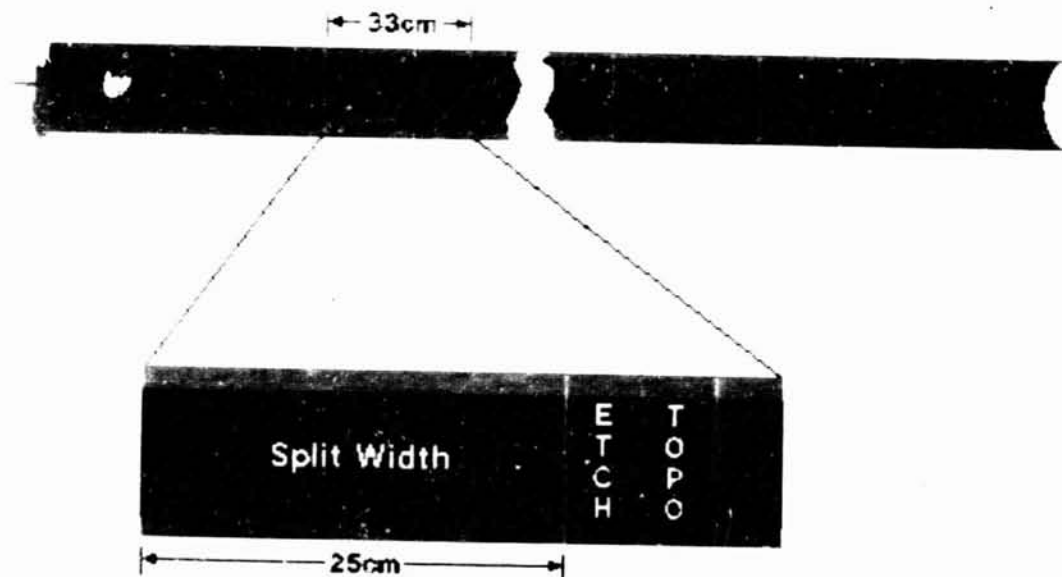
From This Program

- Residual Stress Via Web Split Width Measurements
- Dislocation Density Via Etch Pit Counting
- Defect Type, Distribution And Structure Via X-Ray Topography

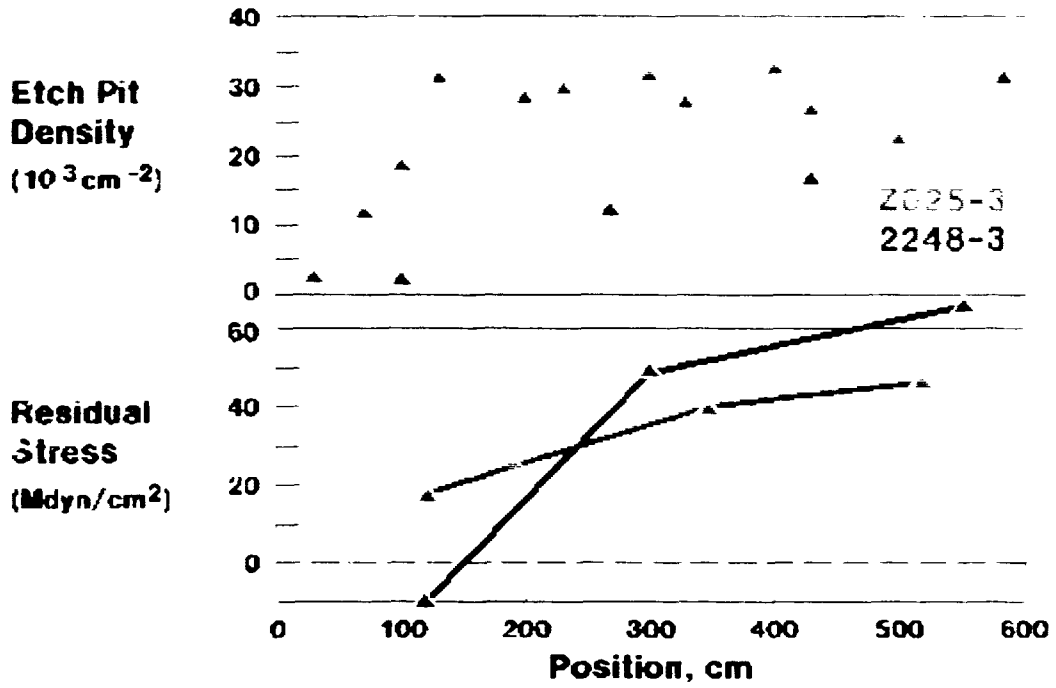
From Associated Programs

- Impurity Evaluation
- Electrical Properties
- Solar Cell Data

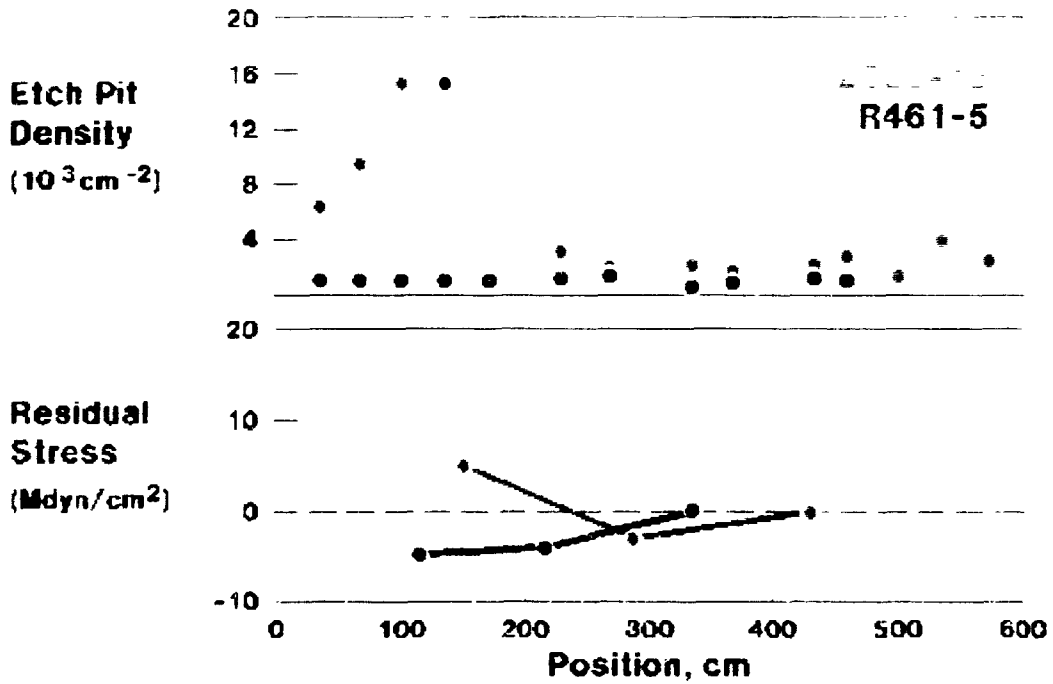
WEB SAMPLES FOR
STRUCTURE ANALYSIS

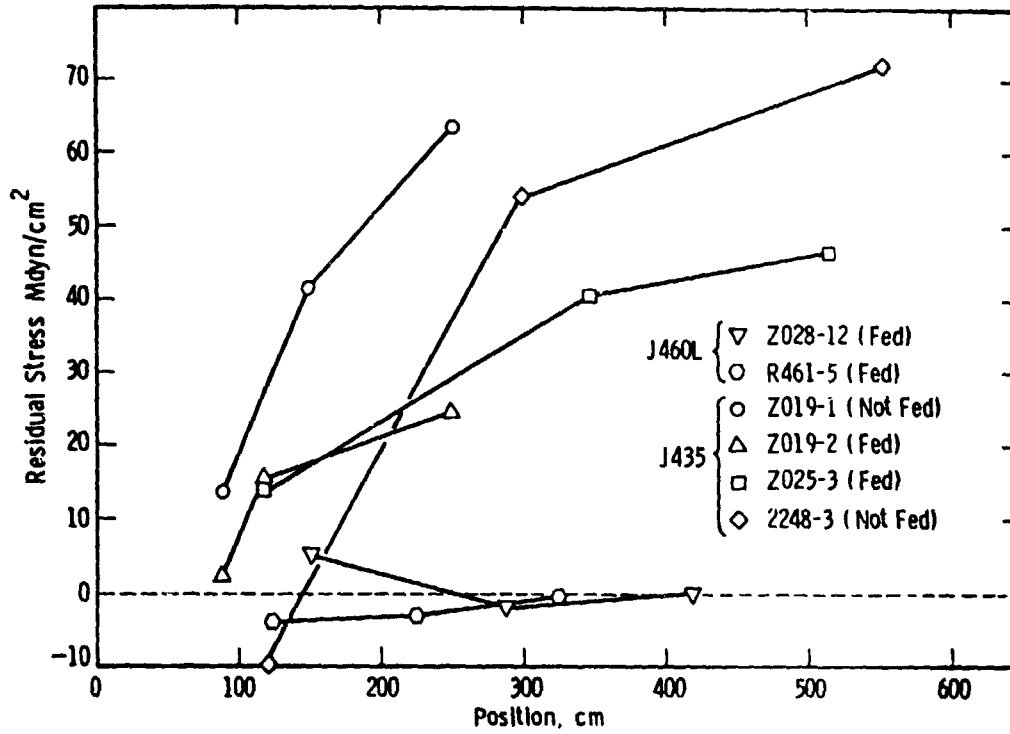


J435 Lid Configuration



J460 Lid Configuration





Problems and Concerns

Calendar Schedule Of Goals Is Tight

Summary

- Technology And Direction Of Development Sufficient To Surpass Goals When Fully Developed
- Major Improvement Achieved In Length Of Continuously Melt Replenished Crystal Growth